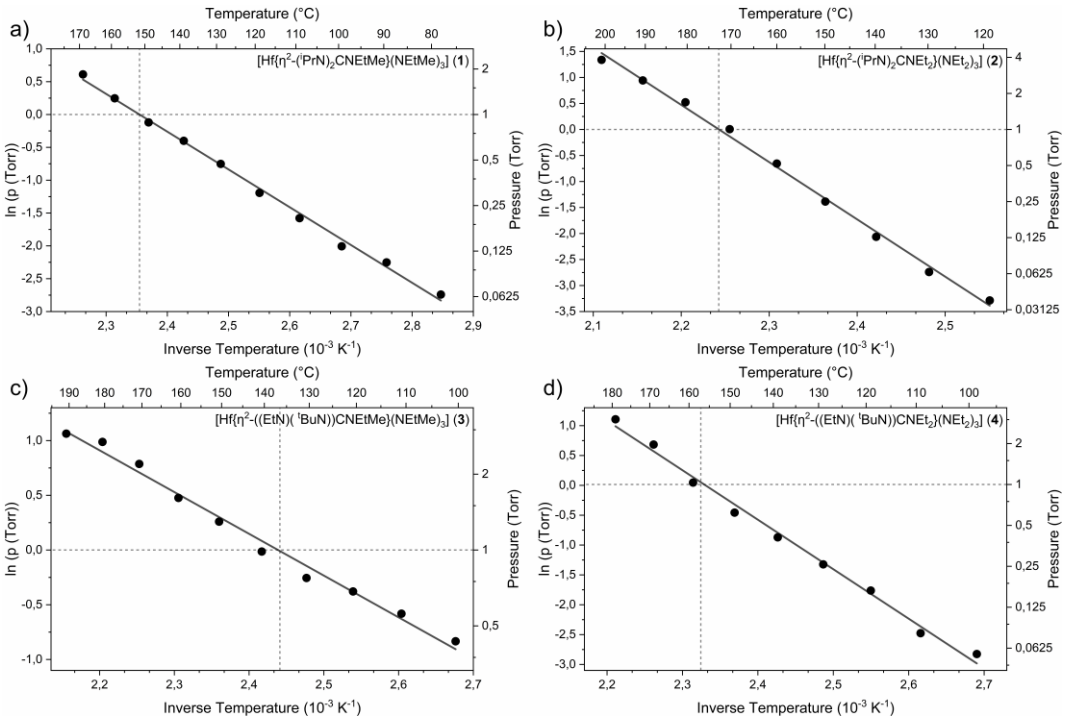

Figure 1: Vapor pressure - temperature correlations of a) [Hf{η^2-(^{i}PrN)$_2$CNEtMe}(NEtMe)$_3$] (**1**); b) [Hf{η^2-(^{i}PrN)$_2$CNEt$_2$}(NEt$_2$)$_3$] (**2**); c) [Hf{η^2-((EtN)(^{t}BuN))CNEtMe}(NEtMe)$_3$] (**3**) and d) [Hf{η^2-((EtN)(^{t}BuN))CNEt$_2$}(NEt$_2$)$_3$] (**4**) according to Langmuir equations estimated by stepped isothermal TGA. 1 Torr vapor pressures are denoted by the intersect of dashed lines. Grey solid lines illustrate the respective linear regression

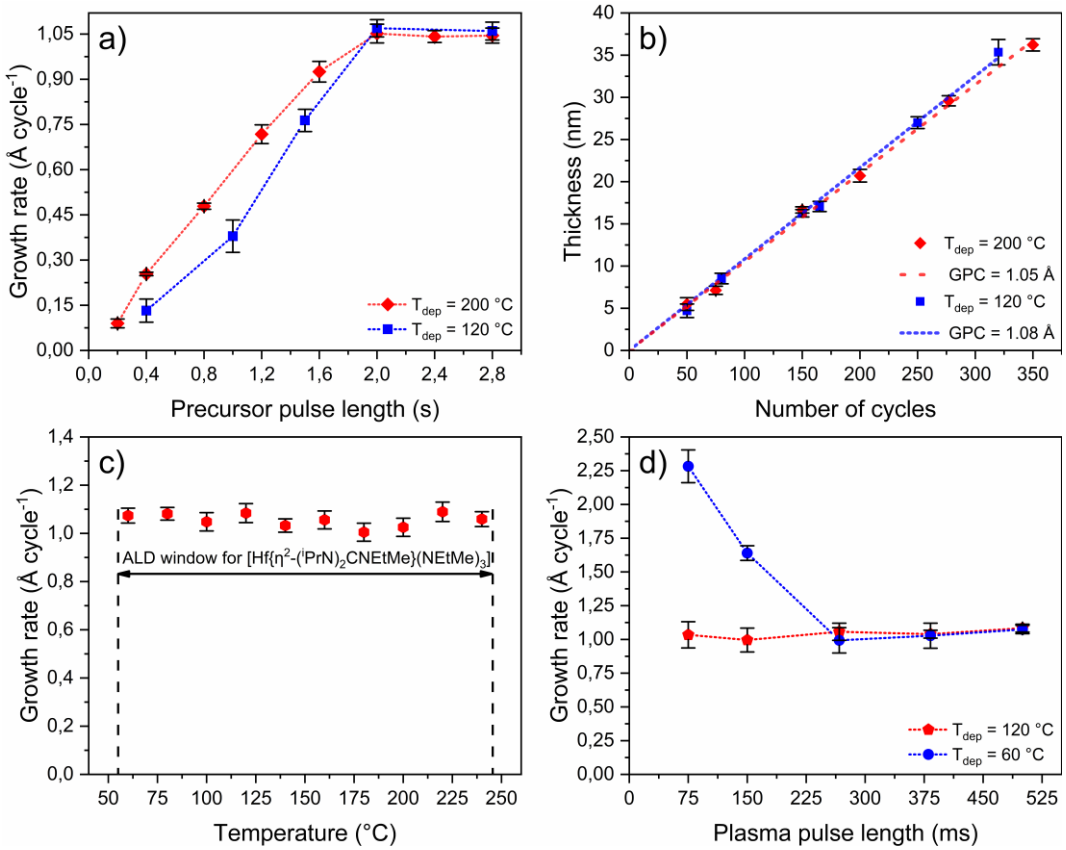

Figure 2: PEALD film growth characteristics on Si(100) employing [Hf{η^2-(^{i}PrN)$_2$CNEtMe}(NEtMe)$_3$] (**1**) and oxygen plasma: a) Saturation study with varying precursor pulse lengths at 120 °C (blue) and 200 °C (red) substrate temperature; b) Film thickness *vs.* applied number of cycles; c) Dependency of film growth on the deposition temperature with a fixed precursor pulse of 2 s and d) influence of the plasma pulse length on the film growth at 60 °C (blue) and 120 °C (red). Dotted lines are shown to guide the eye.